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CMOS Logic

- The basic building of CMOS logic ckt is MOS transistor. As we know, logic ckt is Digital ckt which processes the binary digits i.e. '1' & '0'. However, dual logic ckt processes electrical signals as voltage levels.
- In any logic ckt, there is a range of voltages for Logic '0' & Logic '1'. A typical CMOS operates from 5V power supply. It may have, Logic '0' → 0 to 5V. In b/w these, are the undefined Logic '1' → 3.5 to 5V. Logic levels.

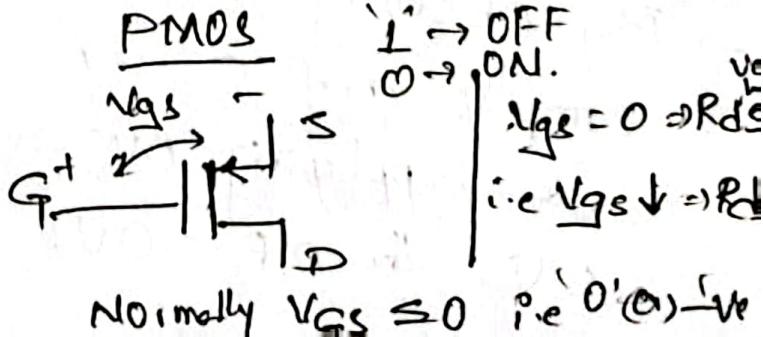
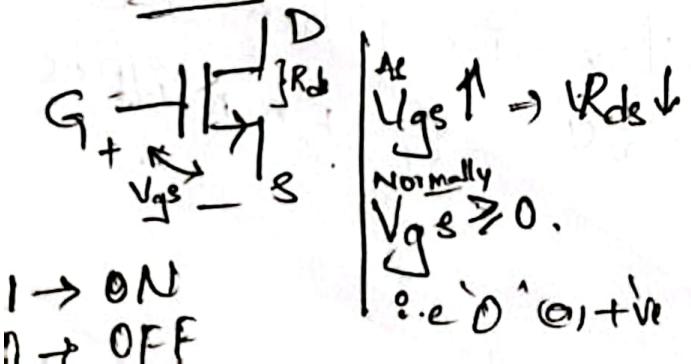
MOS Transistor :- Which is having three terminals G, D, S. As the name it implies the electric field applied at the 'gate' terminal will control the flow of current b/w drain & source.

(i) it will control the resistance b/w S & D, so, it is used as voltage controlled resistance.

→ In digital applications when MOS transistor is 'OFF', then its resistance is 'Very high'; & when it is 'ON', then its resistance "Very low"

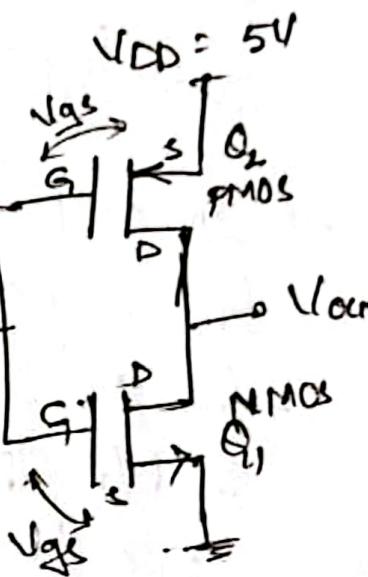
→ There are two types → PMOS
→ NMOS → Is the most widely used

NMOS



Basic CMOS ckt :-

- If, the NMOS & PMOS transistors are connected together in a complementary, then it forms the CMOS Logic
- The simple CMOS ckt is shown in fig:
which is used as an "Inverter." The power supply, V_{DD} typically is $2.6V$ & is most often set at $5V$ for compatibility with TTL. V_{IN} →
- Ideally, the functional behaviour of CMOS can be characterised by two cases.
- When $V_{IN} = 0V$, then NMOS is OFF, since $V_{GS} = 0$, but, PMOS is ON since, $\frac{1}{R_s} V_{GS}$ is a large $+ve$ value ($+5V$). Therefore, Q_2 PMOS have small resistance b/w V_{DD} & V_{OUT} . ∴ the O/P Voltage is $5V$
- When, $V_{IN} = 5V$, then Q_1 NMOS is ON, since $\frac{1}{R_s} V_{GS}$ is a large $-ve$ ($-5V$), but, PMOS is OFF, since $\frac{1}{R_s} V_{GS} \approx 0$. Thus, NMOS, have small resistance b/w O/P & GND, ∴ the O/P Voltage is $0V$
- By observing this functional behaviour it can simply act as an inverter, i.e. When we are applying $0V$, $\rightarrow O/P = 5V$, & when O/P is $5V$; the $O/P = 0V$.



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CMOS NAND & NOR Gate

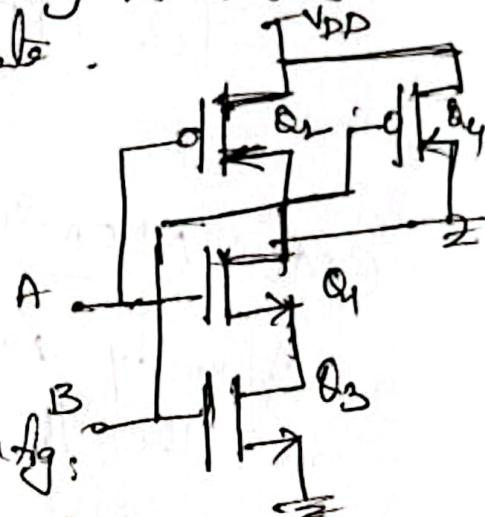
- Both NAND & NOR Gates can be constructed Using CMOS.
- A K-P/P' Gate consists of ' $k \rightarrow \text{NOR}$ ' of p-MOS's & ' $k' \rightarrow \text{NOR}$ ' of n-MOS's.

→ The fig. shows a 2- ℓ /P CMOS NAND gate.

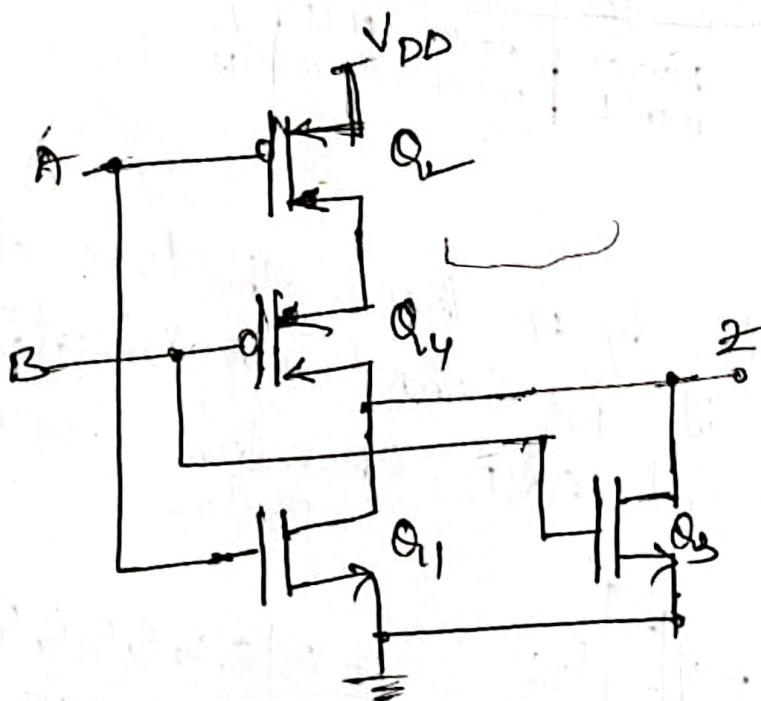
Generally the NAND logic is, if either of P/P' is low, then Q/P is high.

If both the P/P's are high, then the Q/P is 'low'.

The same logic is implemented with CMOS, as shown in fig:



CMOS - NOR Gate



A	B	Q_1	Q_2	Q_3	Z
0	0	OFF	ON	OFF	H
0	1	OFF	OFF	OFF	H
1	0	OFF	OFF	OFF	H
1	1	OFF	OFF	OFF	L

A	B	Q_1	Q_2	Q_3	Z
L	L	OFF	OFF	OFF	H
L	H	OFF	OFF	OFF	L
H	L	OFF	OFF	OFF	L
H	H	OFF	OFF	OFF	L

- If both P/P's are low, then Q/P has low impedance connection to VDD through p-channel MOS, & path to ground is blocked by the OFF N-channel MOS.

- If either P/P is high, the path to VDD is blocked, & 'Z' has low-impedance connection to GND.